

PCB Layout Guidelines for TAS2xxx Series Class-D Boosted Audio Amplifier

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ABSTRACT

As the performance of class-D audio amplifiers gets better and system complexity increases, special care must be taken in the printed circuit board (PCB) layout phase of a design to ensure a robust solution. As in most engineering practices, there is no unique solution to a given problem or unique layout, but this application note helps guide you to reach an optimal layout solution.

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1 Introduction

1.1 Scope

This application note can help system designers implement best practices and understand PCB layout options while designing audio segments of the system. It serves as a guide to laying out critical nets reliably. This helps in extracting best possible audio quality from the class-D audio amplifier. This is intended for the audiences who are involved in designing audio systems.

1.2 Critical Signals

The main concern while designing audio systems includes choosing the right passive component, which maintains quality of the audio, along with small system size and less cost. Another big concern which arises due to SoC IC is routing Analog, Digital, and Power signals with integrity, avoiding interference with each other, and maintaining audio quality. The third concern while routing signals is that other system devices must not interfere with the audio chip and vice versa negatively due to EMI and other voltage and current switching.

Table 1 outlines the signals requiring the most attention when laying out a PCB that incorporates a Texas Instruments boosted audio amplifier System-on-Chip (SoC).

SIGNAL NAME	DESCRIPTION	
BGND	Boost ground. Connect to PCB GND plane.	
DREG	Digital core voltage regulator output. Bypass to GND with a cap. Do not connect to external load.	
GREG	High-side gate CP regulator output. Do not connect to external load.	
GND	Digital ground. Connect to PCB GDN plane	
OUT_N	Class-D negative output for receiver channel	
OUT_P	Class-D positive output for receiver channel	
PGND	Power stage ground. Connect to PCB GND plane.	
PVDD	Power stage supply	
SW	Boost converter switch input	
VBAT	Battery power supply input	
VBST	Boost converter output. Do not connect to external load.	
VDD	Analog, digital, and IO power supply	
VSNS_N	Voltage sense negative input	
VSNS_P	VSNS_P Voltage sense positive input	
ADDR/MODE	Address detect pin	
AVDD	Analog and digital power supply	
IOVDD	IO supply	

Table 1. Critical Signals and Description

2 Layout Guidelines

After selecting the right set of components, the next important task is to lay out the PCB in such a way that the device gives optimum performance for the particular system. A guide to choose right set of passive components for an audio amplifier can be found in the *Passive Component Selection Guide for Class-D Audio Amplifier Application Report*. Four to six layers with epoxy-filled vias is ideal for optimum layout of the device.



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2.1 Power Planes

Power planes must be routed thick enough to carry to the maximum current supply pin demands. Take special care when the supply plane is shared amongst multiple ICs in the system. Best layout practice is providing the planes/thick traces to different ICs in the system from the power management IC or main supply source in a star-connected way at the source itself. This reduces the adverse effect caused on other ICs because of the high switching ICs shared on the same line.

VBST is the output of boost supply and PVDD serves as power supply to output power stage. VBST should be connected to PVDD strongly just below the device on the top layer itself to avoid and voltage droop due to IR losses and ringing due to Via parasitic inductance.

AVDD/VDD and IOVDD must be routed from the PMIC/source as star-connected thick traces (20–30 mils) at the source for several ICs in the system.

Bypass capacitors serve two main purposes. It fulfills the sudden switching current requirement for the device and helps in decoupling voltage noise fluctuations on power pins ensuring reliable constant solid power supply seen by device pin and thus better performance also. In order to reduce parasitic inductance and resistance of the routing, the decoupling capacitors should be placed right next to the corresponding pin on the top layer and route with as thick of trace as possible. For the internal pin where connection to the decoupling capacitor is not possible on top layer, try to route it in immediate layer to top layer to reduce parasitic.

2.2 Ground Plane/Connections

All the ground pins of the devices are expected to be connected to the ground plane as strongly as possible. All the device grounds are expected to be shorted in such a way that there is no formation of multiple ground loops. A direct via on the device pads to the ground plane is preferable. The point to consider here is all the ground pins must be strongly connected to the plane because the logical current return path for different supplies is served by different ground pins (for example, VDD-GND, VBST-BGND, PVDD-PGND, and so forth). A dedicated layer for the ground is strongly recommended. Figure 1 and Figure 2 show an example of the TAS2562 device where all the ground pins are shorted on the top layer just below the device balls and then stitched to ground layer present on layer 2 though multiple vias on the device balls and as close to device balls as possible.

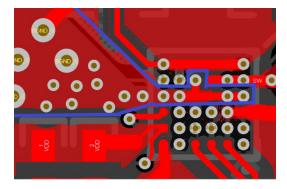


Figure 1. Top Layer for TAS2562 PCB Shows All GND Pins Are Shorted Right at the Device Ball



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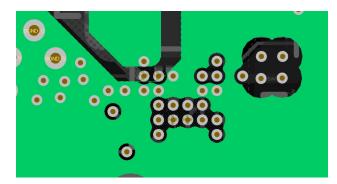


Figure 2. Layer 2 is Solid Ground Just Below the Device Area Also to Provide the Shortest Return Current Path

2.3 Capacitor Placement

Decoupling capacitors must be placed as close to a specific pin on the top layer as possible to avoid parasitic resistance and inductance. Higher resistance and inductance can lead to overshoot/undershoot in the voltage spike due to switching current requirements as per Equation 1.

$$V = -L\frac{di}{dt} \tag{1}$$

For small finite time duration equation can be approximated to:

$$V = -L \frac{\Delta i}{\Delta t} \tag{2}$$

The voltage spikes due to the switching current requirement from the power supplies. Due to the sudden current requirement, even the nH of inductance can cause large voltage ripple and hinder the device operation. Another reason for keeping the parasitic inductance and resistance minimal is to provide the least impedance decoupling path.

The expectation from the system design is that the smallest decoupling cap is placed less than 1 mm of distance from the device pin and any further caps are placed next to it as close as possible.

Parasitic matters for the complete decoupling loop include a parasitic from power supply pin to one end of decoupling capacitor, parasitic of capacitor component, and parasitic between the second end of the capacitor to ground pin of the device. Using multiple vias to connect the capacitor to ground helps in reducing parasitic inductance because of multiple parallel via connections. Vias should be placed as close to capacitor pad as possible. Table 2 shows the total acceptable loop inductance on different supply pins for optimum device performance. It also shows the requirement for the charge pump bootstrap capacitor.

Table 2. Optimum Parasitic on the Device Pin

PIN-PIN	PARASITIC INDUCTANCE (pH)	CAPACITOR ESL (pH)	TOTAL (pH)
DREG-GND	650	500	1150
GREG-PVDD	300	500	800
VBAT-GND	650	500	1150
VBST-BGND	250	500	750
VDD-GND	350	500	850



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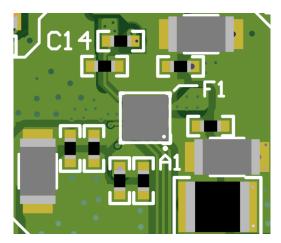


Figure 3. Capacitor Placement for TAS2562 Device as Close to Device as Possible

2.4 Switching Signals

Class-D output, SW node, and Vsense signals are continuously switching signals and should be routed in such a way that so they do not couple and interfere with each other or any other signal on the PCB. They must not be routed in the adjacent layer with any other signal without ground shielding in between layers.

Figure 4, Figure 5, and Figure 6 illustrate the carebout for routing a switching net. Figure 4 shows top level view of the PCB and demonstrates the nets on the different layers. The basic principle here is to avoid coupling between different switching nets and between switching nets and any other signal. Figure 4 and Figure 5 show valid routing conditions while Figure 6 is an invalid scenario.

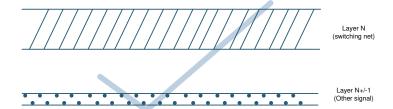


Figure 4. PCB Top View Shows Routing Switching Net Without Providing Cross Sectional Area for Coupling with Other Net in Adjacent Layer

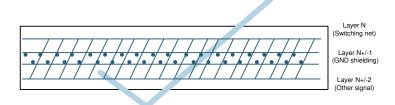


Figure 5. PCB Top View Shows the Decoupling of Switching Net With Other Net by having a Ground Layer Between the Two



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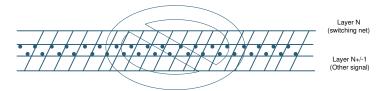


Figure 6. PCB Top View Shows Switching Net Routed Parallel to Other Signal in Adjacent Layer Without Any Ground Shielding Between the Two

2.5 SW

SW refers to the boost switching node which is connected to supply through the boost inductor. The routing of this signal should be capable of carrying 5 A (boost maximum current limit, number varies from device to device) of current and should offer minimum resistance and capacitance between SW and VBAT source in order to avoid efficiency loss.

2.6 Vsense Signals

Vsense signals must be routed as close to speaker terminals as possible. Vsense is used to sense actual voltage across speaker terminals and used for speaker protection. The speaker protection algorithm works optimally if the Vsense is closed closest to speaker terminals. 6 mil trace width is sufficient for these signals and should be routed differentially to avoid any non-differential noise coupling to these signals.

2.7 Charge Pump Capacitor

The charge pump capacitor smust be connected between the GREG/VREG pin and PVDD pin with the least possible parasitic inductance and resistance. Refer to Table 2 for quantitative details. Note that the charge pump capacitor must be connected as close as possible to the PVDD pin as star connection and not on the PVDD plane. Use thick routing and immediate to the top layer for routing this signal to offer minimum parasitic on this pin.

Figure 7, Figure 8, and Figure 9 illustrate the GREG-PVDD routing for the TAS2562 device. GREG is being routed to the PVDD via a capacitor in a star-connected fashion at the PVDD end. Multiple vias are used to connect swap layers and thick GREG trace is used to avoid large parasitic inductance offered by trace.

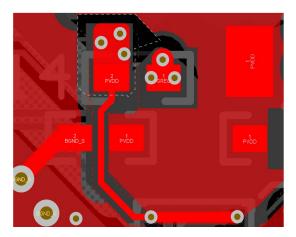


Figure 7. GREG Capacitor on Top Layer, Multiple Vias to Connect to Swap Between Layers to Connect to PVDD, and GREG Device Pin



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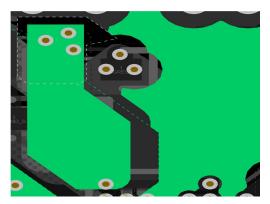


Figure 8. PVDD Routed as Thick Trace to PVDD Device Ball from the Capacitor and Star Connected to PVDD Pin Using a Via

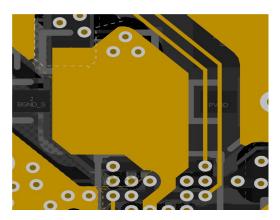


Figure 9. GREG Routed to Device Ball Using a Thick Trace

2.8 Class-D Output Signals

Class-D output signals should be routed at least 30 mil wide in two layers. Effectively, each output must be routed 60 mil wide to the speaker for the EM requirements. In case the EMI filter is placed on the board, it must be placed as close to device pins as possible. For the best THDN performance, output signals should be length matched to each other in order to avoid any mismatch degraded THDN due to difference in routing resistance.

2.9 Digital Signals

Digital signals must be routed in a way so they do not interfere with other signals and their integrity is maintained. Make sure they are not routed adjacent to any switching net, which can couple and inject noise in digital signals.

3 Typical Board Parasitic

For a quick estimation of the parasitic while layout, Table 3 and Table 4 can be quite helpful.

Tables in this section consider the most common fabrication practice of FR-4 STD material, 1-oz of copper, 62 mil PCB thickness, and epoxy-filled via.

Table 3. Resistance and Current Carrying Capability of Output Trace

WIDTH	DC RESISTANCE (mΩ/INCH)	CURRENT CARRYING CAPABILITY (A)
30	9.68	3.18
40	7.08	3.63



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Table 3. Resistance and Current Carrying Capability of Output Trace (continued)

WIDTH	DC RESISTANCE (mΩ/INCH)	CURRENT CARRYING CAPABILITY (A)
50	5.58	4.32
80	3.41	5.55

Table 4. Resistance, Inductance, and Current Carrying Capability of Typical Epoxy-filled Via

VIA DIAMETER (mils) ⁽¹⁾	DC RESISTANCE (m Ω)	INDUCTANCE (nH)	CURRENT CARRYING CABABILITY (A)
4	2.9	1.61	1.4
6	2.1	1.48	1.53
10	1.3	1.32	2.01
12	1.1	1.26	2.21
18	0.7	1.14	2.72

⁽¹⁾ Via properties mentioned in the table are for the complete 62-mil via. In case signals are routed in internal layer, these numbers can be linearly scaled. For example, a 4-mil via offers 0.8-nH inductance between the top layer and a layer 32 mil below the top layer.

4 Summary

This article concludes the optimum layout for a Class-D boosted Audio amplifier. The following table can be used as a checklist for a quick reference while layout.

PIN		
BGND, GND, PGND, GNDD	Short BGND, GND, GNDD, and PGDN below the package and connect them to PCB ground plane strongly through multiple vias. Minimize inductance as much as possible.	
DREG	Bypass to GND with capacitor recommended in section above. Do not connect to external load. Both ends of the decoupling cap should see as low inductance as possible between this pin and GND pins.	
GREG/VREG	Connect it to PVDD with a star connection and not to boost plane with recommended in section above. Do not connect to external load.	
PVDD	Short it to VBST (boost) plane through strong connection. Connect it to GREG with a star connection and not to boost plane.	
SW	Connect to VBAT with boost inductor. Reduce parasitic capacitor and resistance for efficiency. Boost inductor must be as close as possible to the SW pin. The inductor must be connected to SW through thick plane. Traces should support currents up to device boost current limit. No other net should couple to this.	
VBAT	Bypass to GND with a recommended capacitor. Must be connected to the inductor through a thick plane. Both ends of decoupling capacitor should see as low inductance as possible between VBAT pin and PGND pin.	
VBST	Do not connect to external load. Bypass to GND with a recommended capacitor. Connect to PVDD through a thick plane. Both ends of decoupling capacitor should see as low inductance as possible between VBST pin and BGND pin. Traces should support currents up to device overcurrent limit.	
VDD	Bypass to GND with capacitor recommended. Both ends of decoupling cap see as low inductance as possible between this pin and GND pin.	
OUT_P, OUT_N	Should not couple with any other net in the system. Connect EMI filter if required as close to device pin as possible. Traces must support currents up to device overcurrent limit.	

5 References

- Texas Instruments, TAS2562 6.1-W Boosted Class-D Audio Amplifier with IV Sense Datasheet (SLASEI7)
- Texas Instruments, Layout Guidelines For TPA300x Series Parts Application Report (SLOA103)
- Texas Instruments, Post Filter Feedback Class-D Amplifier Benefits and Design Considerations Application Report (SLOA260)



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- Singing Capacitors (Piezoelectric Effect)
- Texas Instruments, Passive Component Selection Guide for Class-D Audio Amplifier Application Report (SLAA903)

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